ŧ

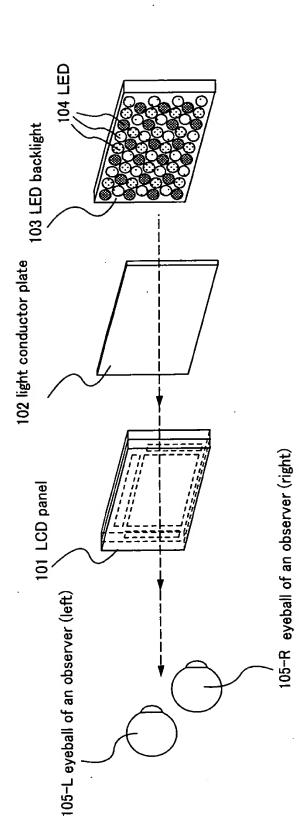


Fig.

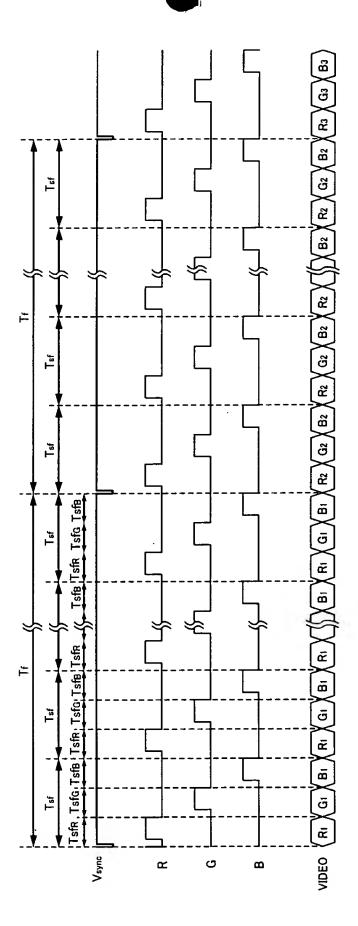


Fig. 2

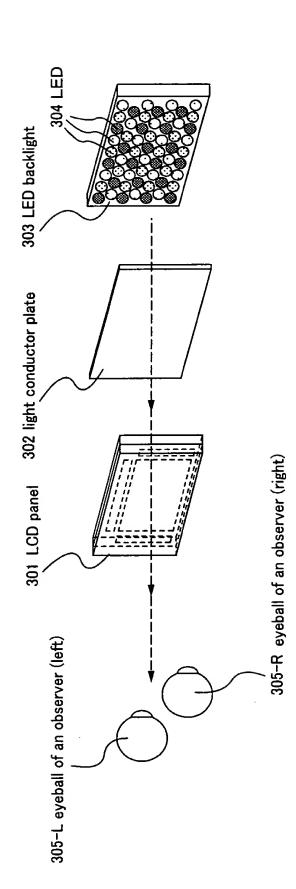


Fig.

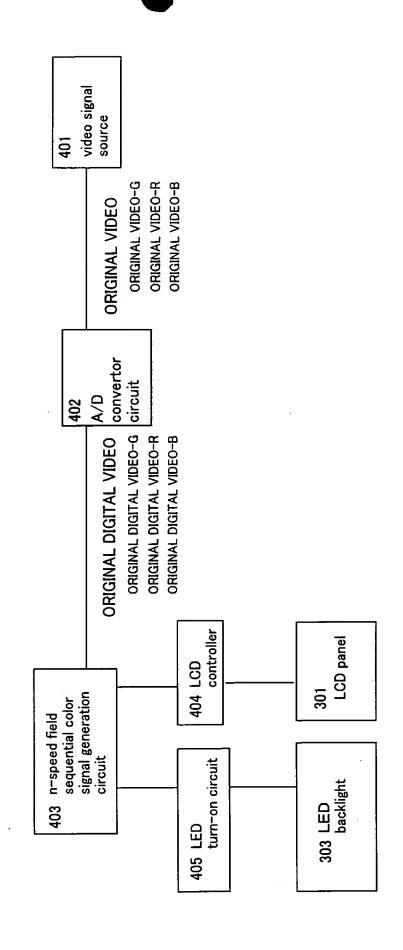


Fig. 4

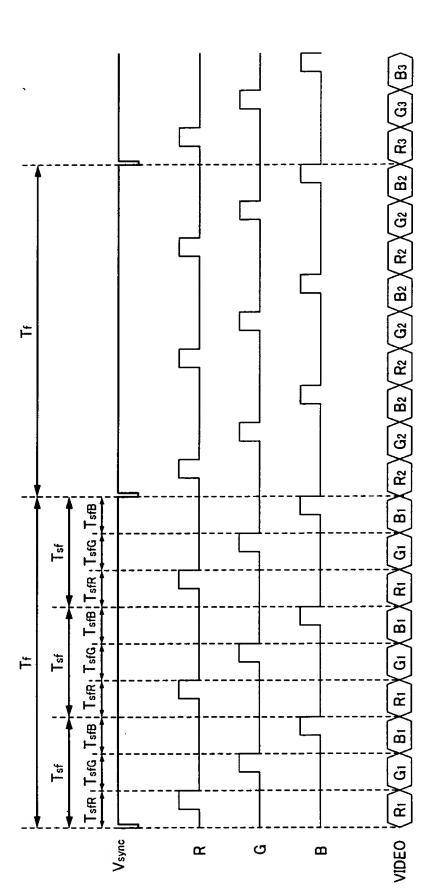


Fig. 5

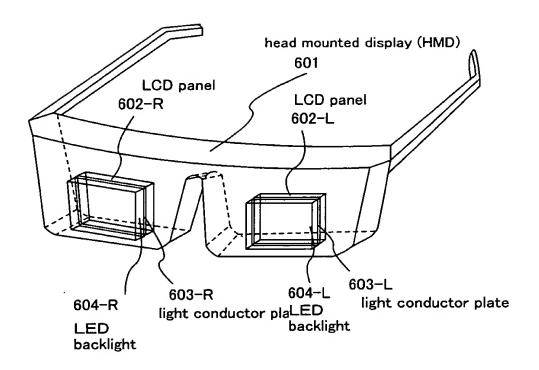
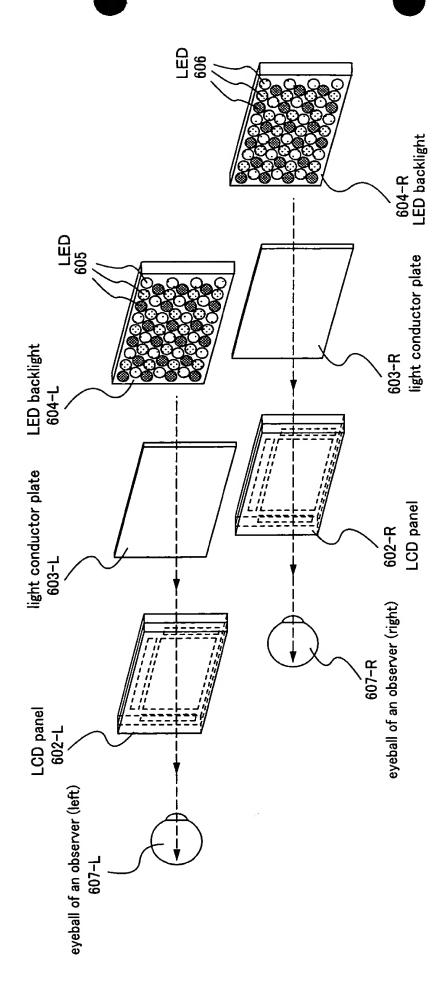


Fig. 6



F18.

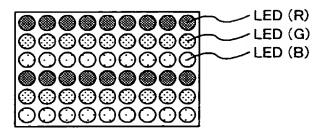


Fig. 8(A)

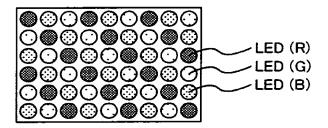


Fig. 8(B)

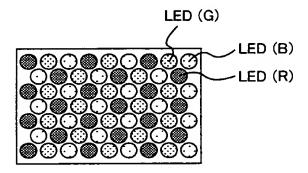


Fig. 8(C)

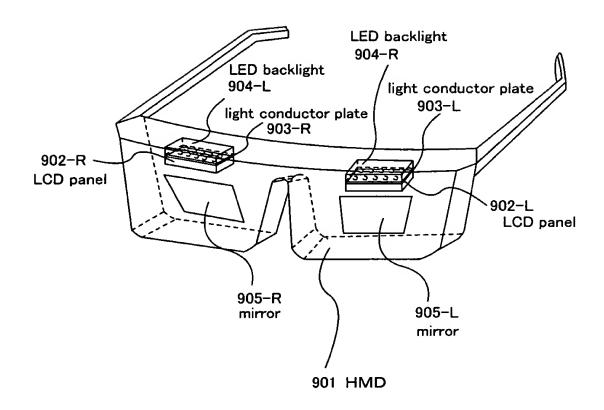


Fig. 9

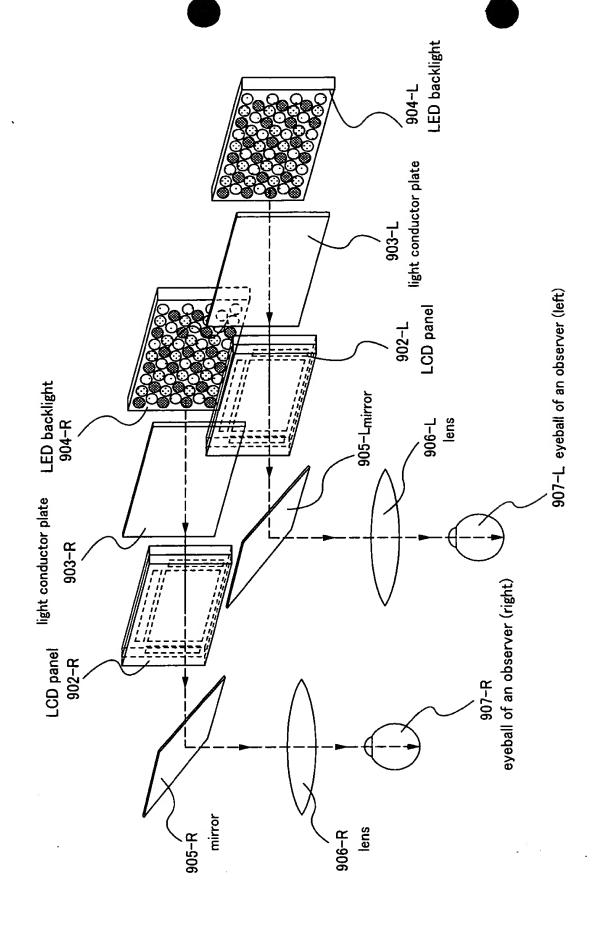


Fig. 10

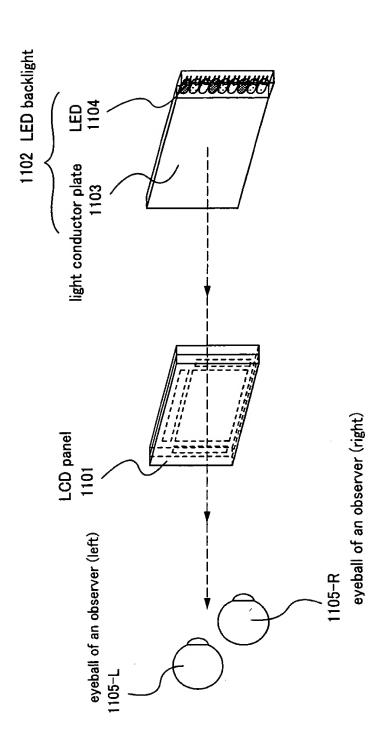


Fig. 11

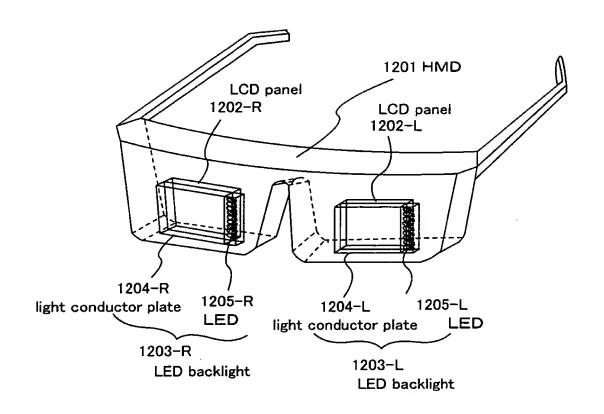


Fig. 12

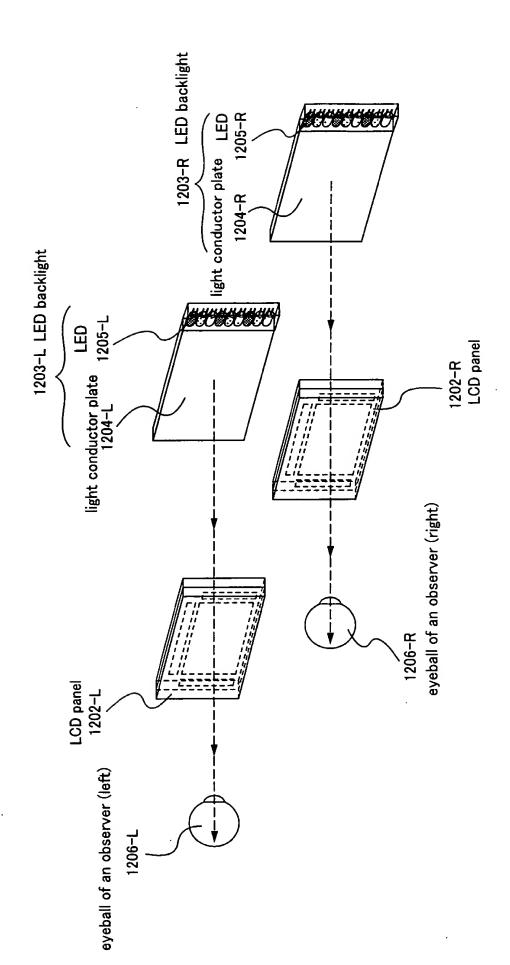
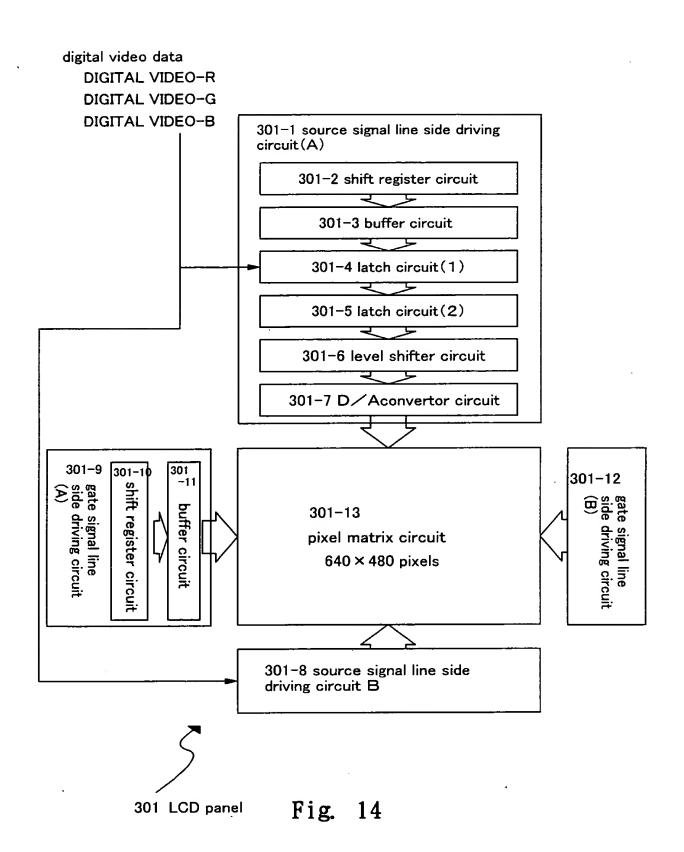


Fig. 13



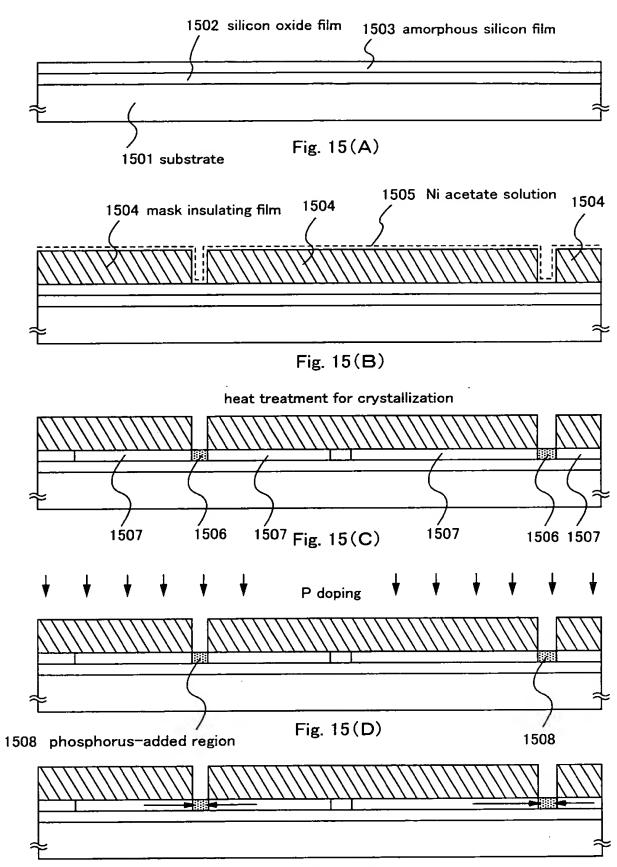
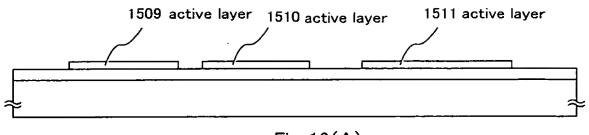


Fig.15(E)





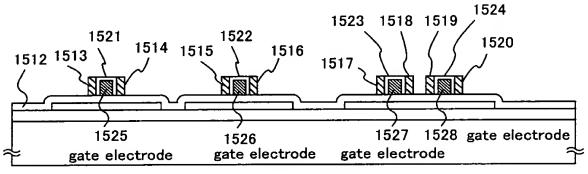


Fig. 16(B)

1513~1520 : porous anodic oxide films

1521~1524 : non-porous anodic oxide films

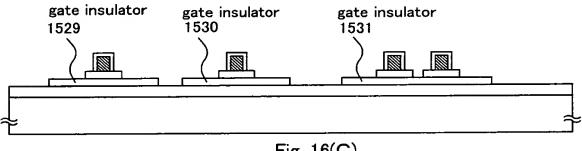
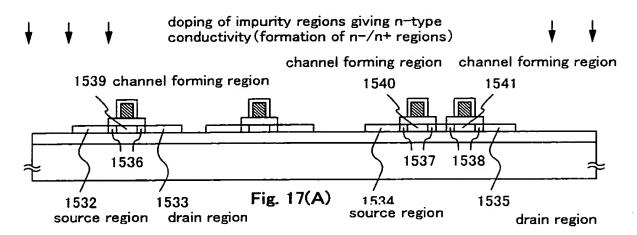


Fig. 16(C)



1536, 1537, 1538: low concentration impurity region

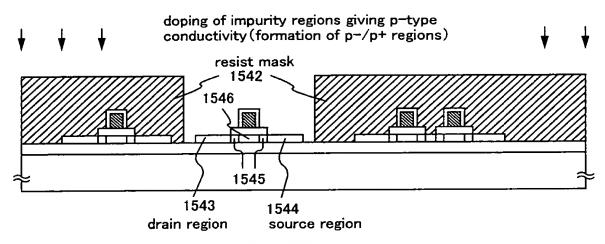


Fig. 17(B) 1545 : low concentration impurity region 1546 : channel forming region

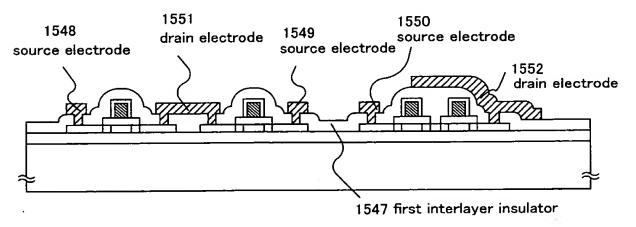


Fig. 17(C)

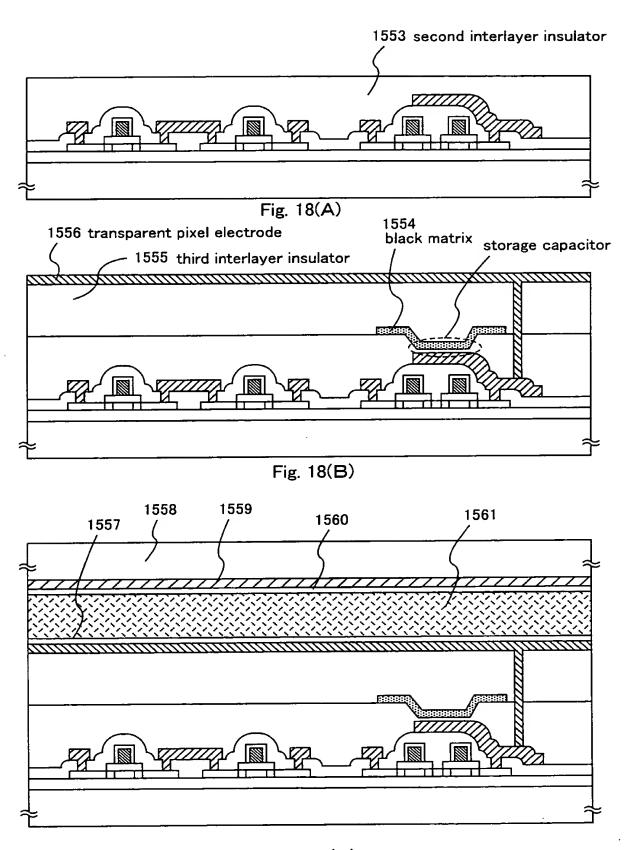
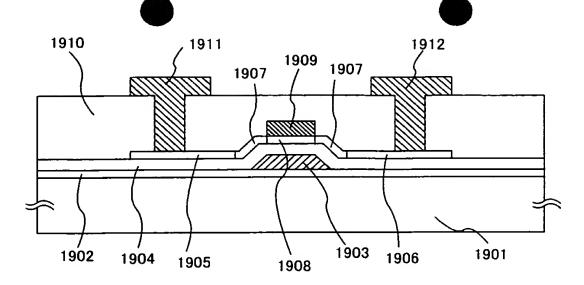


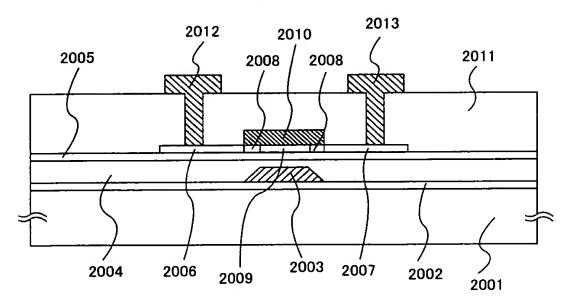
Fig. 18(C)



1901 substrate 1907 LDD

1902 silicon oxide film 1908 channel forming region
1903 gate electrode 1909 channel protecting film
1904 gate insulating film 1910 interlayer insulator
1905 source region 1911 source electrode
1906 drain region 1912 drain electrode

Fig. 19



2001 substrate 2008 (LDD)

2002 silicon oxide film 2009 channel forming region

2003 gate electrode 2010 channel protecting film

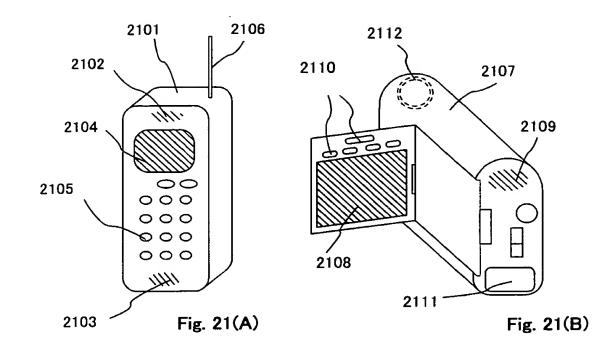
2004 benzocyclobutene(BCB)2011 interlayer insulator

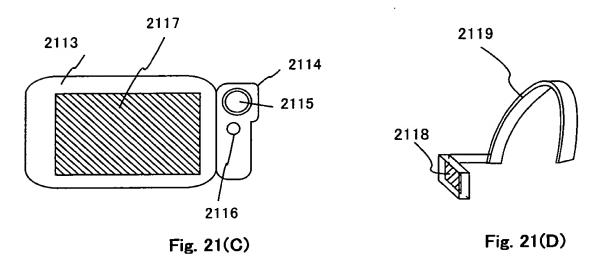
2005 silicon nitride 2012 source electrode

2006 source region 2013 drain electrode

2007 drain region

Fig. 20





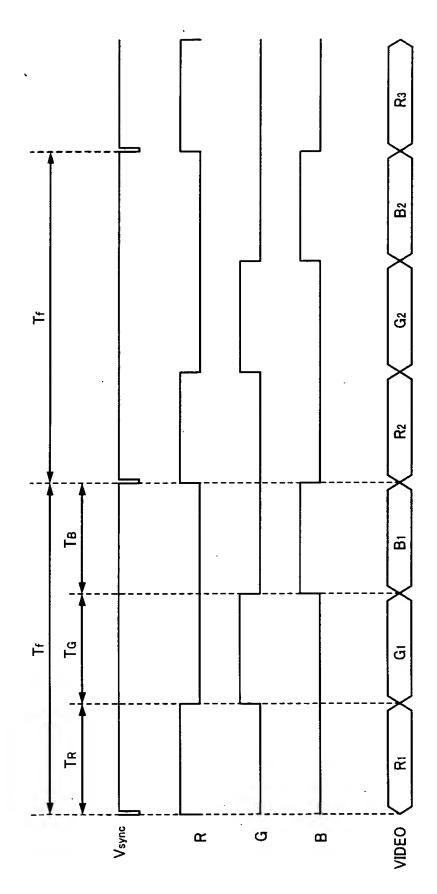


Fig. 22 Prior Art

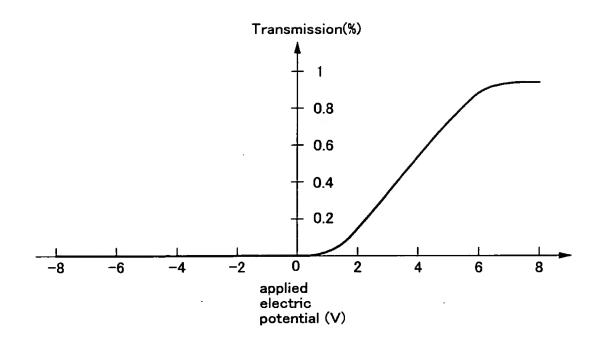


Fig. 23(A)

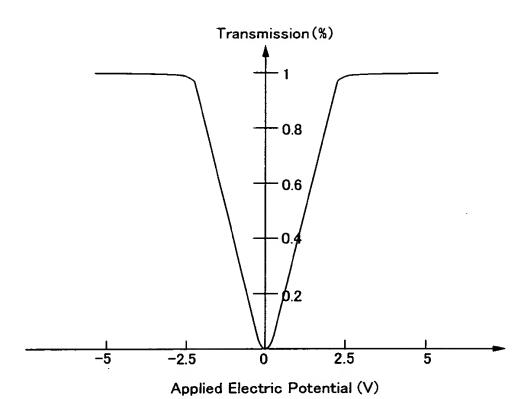
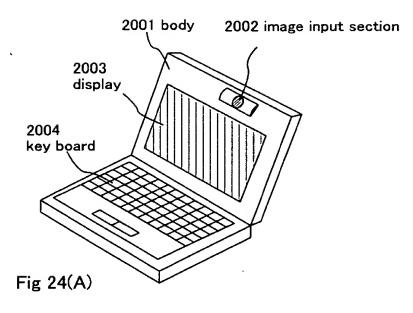


Fig. 23(B)



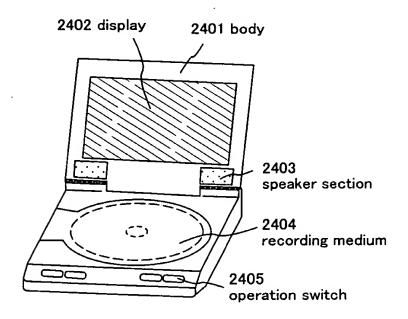


Fig. 24(C)

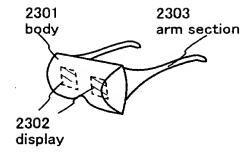


Fig. 24(B)

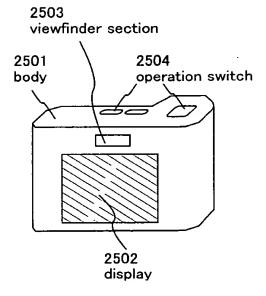


Fig. 24(D)